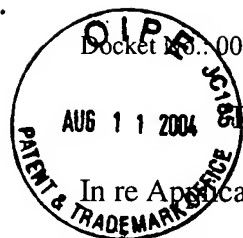


IFW



Docket No. 008019 USA/MTCG/PCTRL

PATENT/OFFICIAL

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Alexander T. SCHWARM

Serial No. 10/759,108

Filed: January 20, 2004

:
:
:
:
: Group Art Unit: 2825
:
: Examiner:

For: AUTOMATED DESIGN AND EXECUTION OF EXPERIMENTS WITH
INTEGRATED MODEL CREATION FOR SEMICONDUCTOR MANUFACTURING
TOOLS

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Honorable Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom. Copies of any cited U.S. Patents and U.S. Patent Publications are not being submitted in accordance with 37 CFR 1.98(a)(2)(i).

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

In accordance with 37 C.F.R. § 1.97(g) and (h), the filing of this IDS should not be construed as a representation that a search had been made or that information cited is, or is considered to be, material to patentability as defined in 37 C.F.R. § 1.56 (b), or that any cited document listed or attached is (or constitutes) prior art. Unless otherwise indicated, the date of

Serial No. 10/759,108

publication indicated for an item is taken from the face of the item, and Applicant reserves the right to prove that the date of publication is in fact different.

No fee is believed to be required; however, the Commissioner is authorized to charge any deficiency in any fees pursuant to 37 CFR § 1.17 associated with this communication and to credit any excess payment to Deposit Account No. 08-0219.

Respectfully submitted,

WILMER CUTLER PICKERING HALE AND DORR LLP



Scott M. Alter


Registration No. 32,879

1455 Pennsylvania Avenue, NW
Washington, DC 20004

TEL 202.942.8428 SMA/lrm

FAX 202.942.8484

Date: 8/11/04

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 008019 USA/ MTCG/PCTRL		SERIAL NO. 10/759,108	
				APPLICANT Alexander T. SCHWARM			
				FILING DATE January 20, 2004		GROUP 2825	
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
	4,957,605	09/18/90	Hurwitt et al.			04/17/89	
	5,240,552	08/31/93	Yu et al.			12/11/91	
	5,369,544	11/29/94	Mastrangelo			04/05/93	
	5,444,837	08/22/95	Bomans et al.			12/29/93	
	5,665,214	09/09/97	Iturralde			05/03/95	
	5,695,810	12/09/97	Dubin et al.			11/20/96	
	5,824,599	10/20/98	Schacham-Diamand et al.			01/16/96	
	5,825,356	10/20/98	Habib et al.			03/18/96	
	5,831,851	11/03/98	Eastburn et al.			03/21/95	
	5,838,951	11/17/98	Song			08/28/96	
	5,859,777	01/12/99	Yokoyama et al.			05/13/97	
	5,871,805	02/16/99	Lemelson			04/08/96	
	5,943,550	08/24/99	Fulford, Jr. et al.			03/29/96	
	6,012,048	01/04/00	Gustin et al.			05/30/97	
	6,037,664	03/14/00	Zhao et al.			03/31/98	
	6,059,636	05/09/00	Inaba et al.			07/09/98	
	6,096,649	08/01/00	Jang			10/25/99	
	6,100,195	08/08/00	Chan et al.			12/28/98	
	6,114,238	09/05/00	Liao			05/20/98	
	6,150,270	11/21/00	Matsuda et al.			01/07/99	
	6,157,864	12/05/00	Schwenke et al.			05/08/98	
	6,181,013 B1	01/30/01	Liu et al.			03/13/00	
	6,212,961 B1	04/10/01	Dvir			02/11/99	
	6,226,563 B1	05/01/01	Lim			09/04/98	
	6,228,280 B1	05/08/01	Li et al.			05/06/98	
	6,237,050 B1	05/22/01	Kim et al.			09/04/98	
	2001/0006873 A1	07/05/01	Moore			02/13/01	
	6,259,160 B1	07/10/01	Lopatin et al.			04/21/99	
	6,281,127 B1	08/28/01	Shue			04/15/99	
EXAMINER			DATE CONSIDERED				

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 008019 USA/ MTCG/PCTRL		SERIAL NO. 10/759,108	
				APPLICANT Alexander T. SCHWARM			
				FILING DATE January 20, 2004		GROUP 2825	
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
	6,317,643 B1	11/13/01	Dmochowski			03/31/99	
	6,339,727 B1	01/15/02	Ladd			12/21/98	
	6,355,559 B1	03/12/02	Havemann et al.			11/03/00	
	6,391,780 B1	05/21/02	Shih et al.			08/23/99	
	6,417,014 B1	07/09/02	Lam et al.			10/19/99	
	6,427,093 B1	07/30/02	Toprac			10/07/99	
	6,432,728 B1	08/13/02	Tai et al.			10/16/00	
	6,449,524 B1	09/10/02	Miller et al.			01/04/00	
	6,455,415 B1	09/24/02	Lopatin et al.			04/16/01	
	2002/0165636 A1	11/07/02	Hasan			04/24/02	
	6,484,064 B1	11/19/02	Campbell			10/05/99	
	6,495,452 B1	12/17/02	Shih			08/18/99	
	2002/0193899 A1	12/19/02	Shanmugasundram et al.			05/01/02	
	2003/0017256 A1	01/23/03	Shimane			06/12/02	
	6,515,368 B1	02/04/03	Lopatin et al.			12/07/01	
	6,517,414 B1	02/11/03	Tobin et al.			03/10/00	
	6,528,409 B1	03/04/03	Lopatin et al.			04/29/02	
	6,537,912 B1	03/25/03	Agarwal			08/25/00	
	6,580,958 B1	06/17/03	Takano			11/22/99	
	6,605,549 B2	08/12/03	Leu et al.			09/29/01	
	6,607,976 B2	08/19/03	Chen et al.			09/25/01	
	6,609,946 B1	08/26/03	Tran			07/14/00	
	6,616,513 B1	09/09/03	Osterheld			04/05/01	
	6,624,075 B1	09/23/03	Lopatin et al.			11/05/02	
	6,630,741 B1	10/07/03	Lopatin et al.			12/07/01	
	6,660,633 B1	12/09/03	Lopatin et al.			02/26/02	
	6,708,074 B1	03/16/04	Chi et al.			08/11/00	
	6,708,075 B2	03/16/04	Sonderman et al.			11/16/01	
	6,728,587 B2	04/27/04	Goldman et al.			12/27/00	
EXAMINER				DATE CONSIDERED			

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 008019 USA/ MTCG/PCTRL		SERIAL NO. 10/759,108			
				APPLICANT Alexander T. SCHWARM					
				FILING DATE January 20, 2004		GROUP 2825			
FOREIGN PATENT DOCUMENTS									
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation			
						Yes	No		
	EP 0 932 195 A1	07/28/99	EP			X			
	EP 1 083 470 A2	03/14/01	EP			X			
	GB 2 365 215 A	02/13/02	GB			X			
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)									
	Sun, S.C. 1998. "CVD and PVD Transition Metal Nitrides as Diffusion Barriers for Cu Metallization." <i>IEEE</i> . pp. 243-246.								
	Tagami, M., A. Furuya, T. Onodera, and Y. Hayashi. 1999. "Layered Ta-nitrides (LTN) Barrier Film by Power Swing Sputtering (PSS) Technique for MOCVD-Cu Damascene Interconnects." <i>IEEE</i> . pp. 635-638.								
	Yamagishi, H., Z. Tokei, G.P. Beyer, R. Donaton, H. Bender, T. Nogami, and K. Maex. 2000. "TEM/SEM Investigation and Electrical Evaluation of a Bottomless I-PVD TA(N) Barrier in Dual Damascene" (Abstract). <i>Advanced Metallization Conference 2000</i> . San Diego, CA.								
	Eisenbraun, Eric, Oscar van der Straten, Yu Zhu, Katharine Dovidenko, and Alain Kaloyeros. 2001. "Atomic Layer Deposition (ALD) of Tantalum-Based Materials for Zero Thickness Copper Barrier Applications" (Abstract). <i>IEEE</i> . pp. 207-209.								
	Smith, S.R., K.E. Elers, T. Jacobs, V. Blaschke, and K. Pfeifer. 2001. "Physical and Electrical Characterization of ALD Tin Used as a Copper Diffusion Barrier in 0.25 μ m, Dual Damascene Backend Structures" (Abstract). <i>Advanced Metallization Conference 2001</i> . Montreal, Quebec.								
	Kim, Y.T. and H. Sim. 2002. "Characteristics of Pulse Plasma Enhanced Atomic Layer Deposition of Tungsten Nitride Diffusion Barrier for Copper Interconnect" (Abstract). <i>IEIC Technical Report</i> . Vol. 102, No. 178, pp. 115-118.								
	Elers, Kai-Erik, Ville Saanila, Pekka J. Soininen, Wei-Min Li, Juhana T. Kostamo, Suvi Haukka, Jyrki Juhanoja, and Wim F.A. Besling. 2002. "Diffusion Barrier Deposition on a Copper Surface by Atomic Layer Deposition" (Abstract). <i>Advanced Materials</i> . Vol. 14, No. 13-14, pp. 149-153.								
	Peng, C.H., C.H. Hsieh, C.L. Huang, J.C. Lin, M.H. Tsai, M.W. Lin, C.L. Chang, Winston S. Shue, and M.S. Liang. 2002. "A 90nm Generation Copper Dual Damascene Technology with ALD TaN Barrier." <i>IEEE</i> . pp. 603-606.								
	Van der Straten, O., Y. Zhu, E. Eisenbraun, and A. Kaloyeros. 2002. "Thermal and Electrical Barrier Performance Testing of Ultrathin Atomic Layer Deposition Tantalum-Based Materials for Nanoscale Copper Metallization." <i>IEEE</i> . pp. 188-190.								
	Wu, Z.C., Y.C. Lu, C.C. Chiang, M.C. Chen, B.T. Chen, G.J. Wang, Y.T. Chen, J.L. Huang, S.M. Jang, and M.S. Liang. 2002. "Advanced Metal Barrier Free Cu Damascene Interconnects with PECVD Silicon Carbide Barriers for 90/65-nm BEOL Technology." <i>IEEE</i> . pp. 595-598.								
	July 25, 2003. International Search Report for PCT/US02/24858.								
	March 30, 2004. Written Opinion for PCT/US02/19062.								
	April 9, 2004. Written Opinion for PCT/US02/19116.								
	April 22, 2004. Office Action for U.S. Serial No. 09/998,372, filed November 30, 2001.								
EXAMINER				DATE CONSIDERED					

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

6